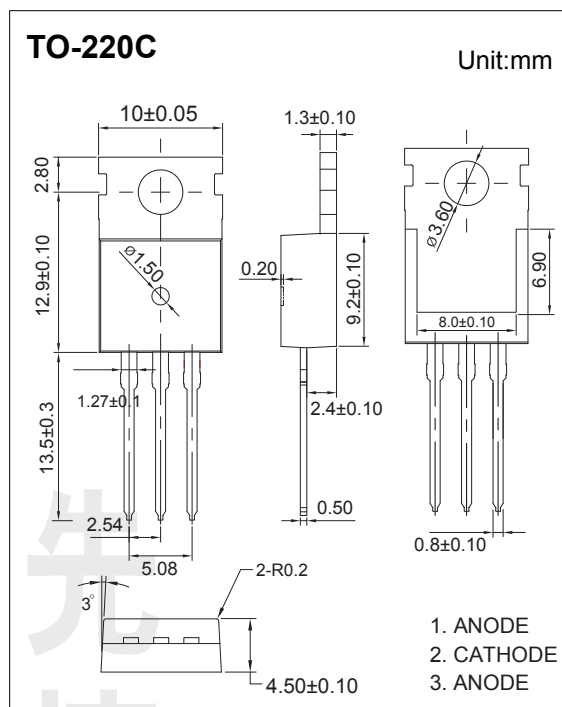


Schottky Barrier Rectifier MBR1070CT~MBR10100CT

■ Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	MBR 1070CT	MBR 1080CT	MBR 1090CT	MBR 10100CT	Unit
Repetitive peak reverse voltage	V_{RRM}	70	80	90	100	V
Working peak reverse voltage	V_{RWM}					
DC blocking voltage	V_R					
RMS reverse voltage	$V_{R(RMS)}$					
Average rectified output current @ $T_c=125^\circ\text{C}$	I_o	10				A
Non-Repetitive peak forward surge current	I_{FSM}	120				
Power dissipation	P_D	2				W
Thermal resistance junction to ambient	$R_{\theta JA}$	50				$^\circ\text{C/W}$
Junction temperature	T_J	125				$^\circ\text{C}$
Storage temperature	T_{STG}	-55 to 150				

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■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Reverse breakdown voltage	MBR1070CT	I _R =0.1mA	70			V
	MBR1080CT		80			
	MBR1090CT		90			
	MBR10100CT		100			
Reverse voltage leakage current	MBR1070CT	V _R =70V			0.1	mA
	MBR1080CT	V _R =80V				
	MBR1090CT	V _R =90V				
	MBR10100CT	V _R =100V				
Forward voltage	V _F	I _F =5A			0.85	V
		I _F =10A			0.95	
Typical total capacitance	C _t	V _R =4V,f=1MHz		150		pF

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■ Typical Characteristics

